

# NCP81382

## Integrated Driver and MOSFET

The NCP81382 integrates a MOSFET driver, high-side MOSFET and low-side MOSFET into a single package.

The driver and MOSFETs have been optimized for high-current DC-DC buck power conversion applications. The NCP81382 integrated solution greatly reduces package parasitics and board space compared to a discrete component solution.

### Features

- Capable of Average Currents up to 35 A
- Capable of Switching at Frequencies up to 2 MHz
- Capable of Peak Currents up to 70 A
- Compatible with 3.3 V or 5 V PWM Input
- Responds Properly to 3-level PWM Inputs
- Option for Zero Cross Detection with 3-level PWM
- ZCD\_EN Input for Diode Emulation with 2-level PWM
- Internal Bootstrap Diode
- Undervoltage Lockout
- Supports Intel® Power State 4
- Thermal Warning output
- Thermal Shutdown
- This is a Pb-Free Device

### Applications

- Desktop & Notebook Microprocessors

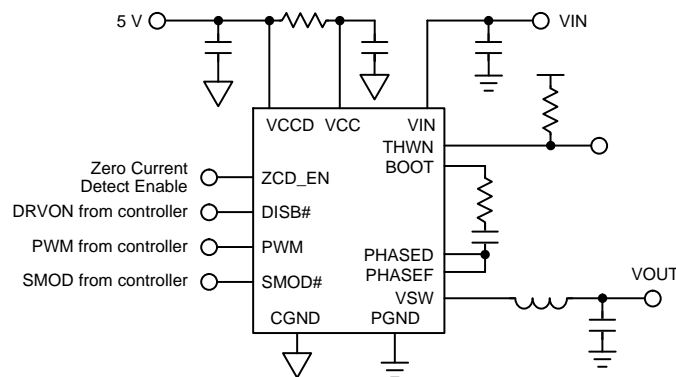


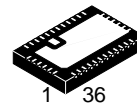
Figure 1. Application Schematic



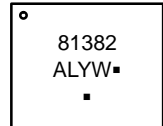
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

### MARKING DIAGRAM



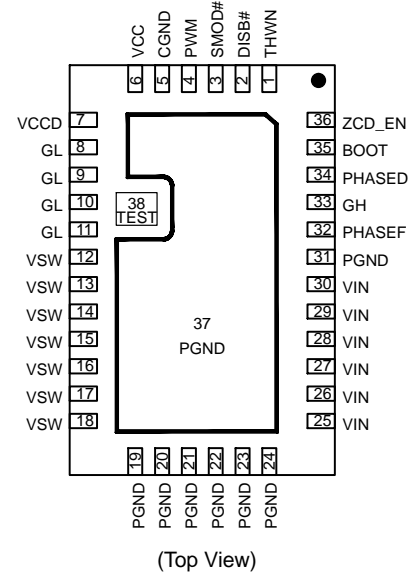
QFN36 6x4  
CASE 485DZ



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

### PINOUT DIAGRAM



(Top View)

### ORDERING INFORMATION

Device	Package	Shipping†
NCP81382MNTXG	QFN36 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



# NCP81382

## PIN LIST AND DESCRIPTIONS (continued)

Pin No.	Symbol	Description
19	PGND	Power Ground
20	PGND	Power Ground
21	PGND	Power Ground
22	PGND	Power Ground
23	PGND	Power Ground
24	PGND	Power Ground
25	VIN	Conversion Supply Power Input
26	VIN	Conversion Supply Power Input
27	VIN	Conversion Supply Power Input
28	VIN	Conversion Supply Power Input
29	VIN	Conversion Supply Power Input
30	VIN	Conversion Supply Power Input
31	PGND	Power Ground
32	PHASEF	Bootstrap Capacitor Return (must be connected to PHASED)
33	GH	High Side FET Gate Access
34	PHASED	Driver Phase Connection (must be connected to PHASEF)
35	BOOT	Bootstrap Voltage
36	ZCD_EN	PWM drive logic and zero current detection enable. 3-state input: PWM = High → GH is high, GL is low. PWM = Mid → Diode emulation mode. PWM = Low → GH is low. State of GL is dependent on states of SMOD# and ZCD_EN (see Table 1 LOGIC TABLE).
37	PGND	Power Ground
38	TEST	No connection should be made to this pin. No pad is needed on the PCB footprint

## ABSOLUTE MAXIMUM RATINGS (Electrical Information – all signals referenced to PGND unless noted otherwise) (Note 1)

Pin Name	Min	Max	Unit
VCC, VCCD	-0.3	6.5	V
GH to PHASED (DC)	-0.3	$V_{BOOT} - V_{SW} + 0.3$	V
GH to PHASED (< 50 ns)	-5.0	7.7	V
VIN	-0.3	30	V
BOOT (DC)	-0.3	35	V
BOOT (< 20 ns)	-0.3	40	V
BOOT to PHASED (DC)	-0.3	6.5	V
VSW, PHASED, PHASEF (DC)	-0.3	30	V
VSW, PHASED, PHASEF (< 20 ns)	-1.0	-	V
VSW, PHASED, PHASEF (< 5 ns)	-5.0	37	V
All Other Pins	-0.3	$V_{VCC} + 0.3$	V
Single-Pulse Drain-to-Source Avalanche Energy, High-Side FET ( $T_J = 25^\circ\text{C}$ , $V_{GS} = 5\text{ V}$ , $L = 0.1\text{ mH}$ , $R_G = 25\ \Omega$ , $I_L = 54\text{ A}_{PK}$ )	-	144	mJ
Single-Pulse Drain-to-Source Avalanche Energy, Low-Side FET ( $T_J = 25^\circ\text{C}$ , $V_{GS} = 5\text{ V}$ , $L = 0.3\text{ mH}$ , $R_G = 25\ \Omega$ , $I_L = 31.5\text{ A}_{PK}$ )	-	180	mJ
Single-Pulse Drain-to-Source Avalanche Energy, High-Side FET ( $T_J = 25^\circ\text{C}$ , $L = 0.15\ \mu\text{H}$ , $I_L = 90\text{ A}_{PK}$ , $V_{DS}\text{ dV/dt} = 30\text{ V} / 2\text{ ns}$ )	-	200	$\mu\text{J}$
Single-Pulse Drain-to-Source Avalanche Energy, Low-Side FET ( $T_J = 25^\circ\text{C}$ , $L = 150\text{ nH}$ , $I_L = 90\text{ A}_{PK}$ , $V_{DS}\text{ dV/dt} = 30\text{ V} / 4\text{ ns}$ )	-	200	$\mu\text{J}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Absolute Maximum Ratings are not tested in production.

# NCP81382

## THERMAL INFORMATION

Rating	Symbol	Value	Unit
Thermal Resistance	$\theta_{JA}$	22	°C/W
	$R\Psi_{J-BT}$	2	°C/W
	$R\Psi_{J-CT}$	4	°C/W
Operating Junction Temperature Range (Note 2)	$T_J$	-40 to +150	°C
Operating Ambient Temperature Range		-40 to +125	°C
Maximum Storage Temperature Range	$T_{STG}$	-40 to +150	°C
Maximum Power Dissipation		10	W
Moisture Sensitivity Level	MSL	3	

- The maximum package power dissipation must be observed.
- JESD 51-5 (1S2P Direct-Attach Method) with 0 LFM
- JESD 51-5 (1S2P Direct-Attach Method) with 0 LFM
- JESD 51-7 (1S2P Direct-Attach Method) with 0 LFM

## RECOMMENDED OPERATING CONDITIONS

Parameter	Pin Name	Conditions	Min	Typ	Max	Unit
Supply Voltage Range	VCC, VCCD		4.5	5.0	5.5	V
Conversion Voltage	VIN		4.5	12	20	V
Continuous Output Current		$F_{SW} = 1 \text{ MHz}, V_{IN} = 12 \text{ V}, V_{OUT} = 1.1 \text{ V}$			30	A
		$F_{SW} = 500 \text{ kHz}, V_{IN} = 12 \text{ V}, V_{OUT} = 1.1 \text{ V}$			35	A
Peak Output Current		$F_{SW} = 500 \text{ kHz}, V_{IN} = 12 \text{ V}, V_{OUT} = 1.1 \text{ V},$ Duration = 10 ms, Period = 1 s			70	A
Operating Temperature			-40		100	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## ELECTRICAL CHARACTERISTICS

( $V_{VCC} = V_{VCCD} = 5.0 \text{ V}, V_{VIN} = 12 \text{ V}, V_{DISB\#} = 2.0 \text{ V}, C_{VCCD} = C_{VCC} = 0.1 \mu\text{F}$  unless specified otherwise) Min/Max values are valid for the temperature range  $-40^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$  unless noted otherwise, and are guaranteed by test, design or statistical correlation.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
-----------	--------	------------	-----	-----	-----	------

### VCC SUPPLY CURRENT

Operating		DISB# = 5 V, ZCD_EN = 5 V, PWM = 400 kHz	-	1	2	mA
No switching, ZCD enabled		DISB# = 5 V, ZCD_EN = 5 V, PWM = 0 V	-	-	2	mA
No switching, ZCD disabled		DISB# = 5 V, ZCD_EN = 0 V, PWM = 0 V	-	-	1.8	mA
Disabled		DISB# = 0 V ZCD_EN = VCC, SMOD# = VCC	-	0.1	1	$\mu\text{A}$
		DISB# = 0 V ZCD_EN = VCC, SMOD# = GND		10	13	$\mu\text{A}$
		DISB# = 0 V ZCD_EN = SMOD# = GND	-	27	40	$\mu\text{A}$
UVLO Start Threshold	$V_{UVLO}$	VCC rising	2.9	-	3.3	V
UVLO Hysteresis			150	-	-	mV

### VCCD SUPPLY CURRENT

Operating		DISB# = 5 V, ZCD_EN = 5 V, PWM = 400 kHz	-	-	20	mA
-----------	--	---	---	---	----	----

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NCP81382

## ELECTRICAL CHARACTERISTICS (continued)

( $V_{VCC} = V_{VCCD} = 5.0\text{ V}$ ,  $V_{VIN} = 12\text{ V}$ ,  $V_{DISB\#} = 2.0\text{ V}$ ,  $C_{VCCD} = C_{VCC} = 0.1\ \mu\text{F}$  unless specified otherwise) Min/Max values are valid for the temperature range  $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$  unless noted otherwise, and are guaranteed by test, design or statistical correlation.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
-----------	--------	------------	-----	-----	-----	------

### VCCD SUPPLY CURRENT

Enabled, No switching		DISB# = 5 V, PWM = 0 V, $V_{PHASED} = 0\text{ V}$	–	175	300	$\mu\text{A}$
Disabled		DISB# = 0 V	–	0.1	1	$\mu\text{A}$

### DISB# INPUT

Input Resistance		To Ground, @ 25°C	–	461	–	k $\Omega$
Upper Threshold	$V_{UPPER}$		–	–	2.0	V
Lower Threshold	$V_{LOWER}$		0.8	–	–	V
Hysteresis		$V_{UPPER} - V_{LOWER}$	200	–	–	mV
Enable Delay Time	$t_{ENABLE}$	Time from DISB# transitioning HI to when VSW responds to PWM.	–	–	40	$\mu\text{s}$
Disable Delay Time	$t_{DISABLE}$	Time from DISB# transitioning LOW to when both output FETs are off.	–	25	50	ns

### PWM INPUT

Input High Voltage	$V_{PWM\_HI}$		2.65	–	–	V
Input Mid-state Voltage	$V_{PWM\_MID}$		1.4	–	2.0	V
Input Low Voltage	$V_{PWM\_LO}$		–	–	0.7	V
Input Resistance	$R_{PWM\_HIZ}$	SMOD# = $V_{SMOD\#\_HI}$ or $V_{SMOD\#\_LO}$	10	–	–	M $\Omega$
Input Resistance	$R_{PWM\_BIAS}$	SMOD# = $V_{SMOD\#\_MID}$	–	63	–	k $\Omega$
PWM Input Bias Voltage	$V_{PWM\_BIAS}$	SMOD# = $V_{SMOD\#\_MID}$	–	1.7	–	V
PWM Propagation Delay, Rising	$tpd_{GL}$	PWM = 2.25 V to GL = 90%; SMOD# = LOW	–	25	35	ns
PWM Propagation Delay, Falling	$tpd_{GH}$	PWM = 0.75 V to GH = 90%	–	15	25	ns
Exiting PWM Mid-state Propagation Delay, Mid-to-Low	$T_{PWM\_EXIT\_L}$	PWM = Mid-to-Low to GL = 10%, ZCD_EN = High	–	13	25	ns
Exiting PWM Mid-state Propagation Delay, Mid-to-High	$T_{PWM\_EXIT\_H}$	PWM = Mid-to-High to GH = 10%	–	13	25	ns

### SMOD# INPUT

SMOD# Input Voltage High	$V_{SMOD\_HI}$		2.65	–	–	V
SMOD# Input Voltage Mid-state	$V_{SMOD\#\_MID}$		1.4	–	2.0	V
SMOD# Input Voltage Low	$V_{SMOD\_LO}$		–	–	0.7	V
SMOD# Input Resistance	$R_{SMOD\#\_UP}$	Pull-up resistance to VCC	–	440	–	k $\Omega$
SMOD# Propagation Delay, Falling	$T_{SMOD\#\_PD\_F}$	SMOD# = Low to GL = 90%, PWM = Low	–	26	30	ns
SMOD# Propagation Delay, Rising	$T_{SMOD\#\_PD\_R}$	SMOD# = High to GL = 10%, ZCD_EN = High, PWM = Low	–	15	30	ns

### ZCD\_EN INPUT

ZCD_EN Input Voltage High	$V_{ZCD\_EN\_HI}$		2.0	–	–	V
ZCD_EN Input Voltage Low	$V_{ZCD\_EN\_LO}$		–	–	0.8	V
ZCD_EN Hysteresis	$V_{ZCD\_EN\_HYS}$		–	250	–	mV
ZCD_EN Input Resistance	$R_{ZCD\_EN\_PU}$	to VCC	–	270	–	k $\Omega$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NCP81382

## ELECTRICAL CHARACTERISTICS (continued)

( $V_{VCC} = V_{VCCD} = 5.0\text{ V}$ ,  $V_{VIN} = 12\text{ V}$ ,  $V_{DISB\#} = 2.0\text{ V}$ ,  $C_{VCCD} = C_{VCC} = 0.1\text{ }\mu\text{F}$  unless specified otherwise) Min/Max values are valid for the temperature range  $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$  unless noted otherwise, and are guaranteed by test, design or statistical correlation.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
-----------	--------	------------	-----	-----	-----	------

### ZCD\_EN INPUT

ZCD_EN Propagation Delay, Rising	$T_{ZCD\_EN,PD\_R}$	SMOD# = High, ZCD_EN = High to GL = 10%	–	40	45	ns
ZCD_EN Propagation Delay, Falling	$T_{ZCD\_EN,PD\_F}$	SMOD# = High, ZCD_EN = Low to GL = 90%	–	25	40	ns

### ZCD FUNCTION

Zero Cross Detect Threshold	$V_{ZCD}$		–	–6.5	–	mV
ZCD Blanking + Debounce Time	$t_{BLNK}$		–	330	–	ns

### NON-OVERLAP DELAYS

Non-overlap Delay, Leading Edge	$t_{pdhGH}$	GL Falling = 1 V to GH-VSW Rising = 1 V	–	13	–	ns
Non-overlap Delay, Trailing Edge	$t_{pdhGL}$	GH-VSW Falling = 1 V to GL Rising = 1 V	–	12	–	ns

### THERMAL WARNING & SHUTDOWN

Thermal Warning Temperature	$T_{THWN}$	Temperature at Driver Die	–	150	–	$^{\circ}\text{C}$
Thermal Warning Hysteresis	$T_{THWN\_HYS}$		–	15	–	$^{\circ}\text{C}$
Thermal Shutdown Temperature	$T_{THDN}$	Temperature at Driver Die	–	180	–	$^{\circ}\text{C}$
Thermal Shutdown Hysteresis	$T_{THDN\_HYS}$		–	25	–	$^{\circ}\text{C}$
THWN Open Drain Current	$I_{THWN}$		–	–	5	mA

### BOOSTSTRAP DIODE

Forward Voltage		Forward Bias Current = 2.0 mA	–	300	–	mV
-----------------	--	-------------------------------	---	-----	---	----

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

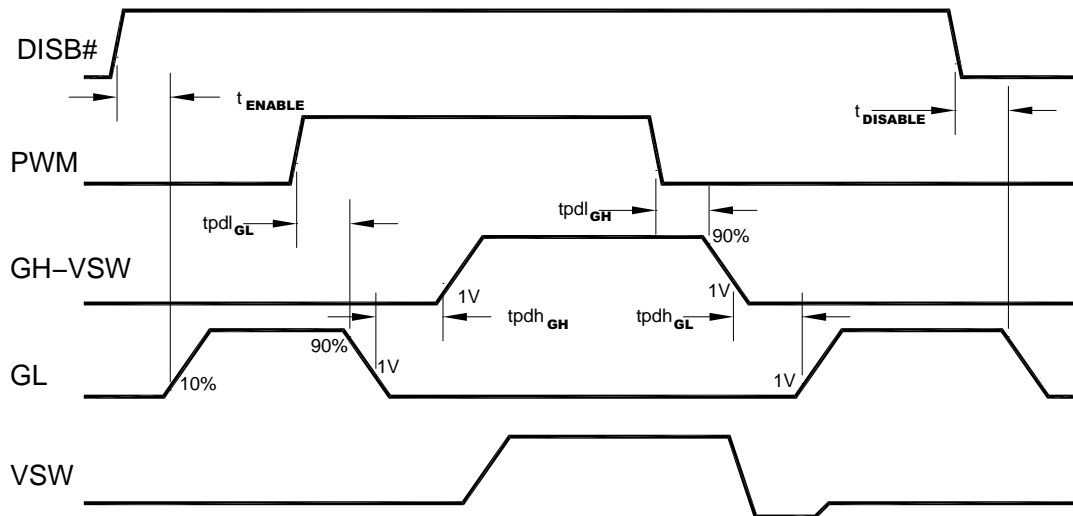


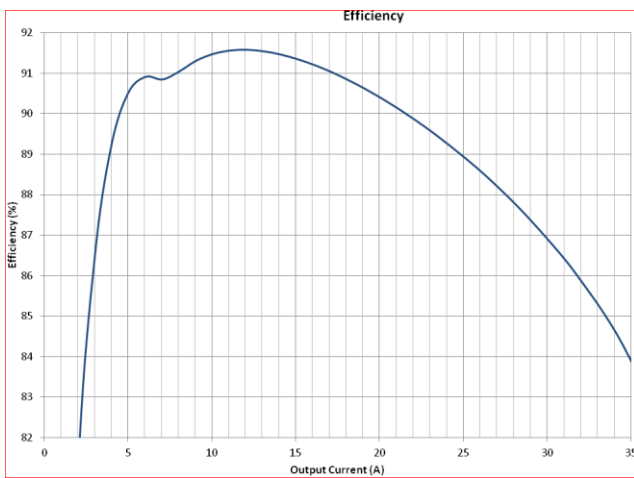
Figure 3. Timing Diagram

# NCP81382

**Table 1. LOGIC TABLE**

INPUT TRUTH TABLE					
DISB#	PWM	SMOD# (Note 5)	ZCD_EN	GH	GL
L	X	X	X	L	L
H	H	X	X	H	L
H	L	X	L	L	L
H	L	X	H	L	H
H	MID	H or MID	H	L	ZCD (Note 6)
H	MID	X	L	L	L (Note 7)
H	MID	L	X	L	L (Note 7)

5. PWM input is driven to mid-state with internal divider resistors when SMOD# is driven to mid-state and PWM input is undriven externally.
6. GL goes low following 80 ns de-bounce time, 250 ns blanking time and then SW exceeding ZCD threshold.
7. There is no delay before GL goes low.



**Figure 4. Efficiency – 12 V Input, 1.2 V Output, 500 kHz**



**Figure 5. Efficiency – 19 V Input, 1.2 V Output, 500 kHz**

## APPLICATIONS INFORMATION

**Theory of Operation**

The NCP81382 is an integrated driver and MOSFET module designed for use in a synchronous buck converter topology. The NCP81382 supports numerous application control definitions including ZCD (Zero Current Detect) with Pin enable and alternately PWM Tristate control. A PWM input signal is required to control the drive signals to the high-side and low-side integrated MOSFETs.

**Low-Side Driver**

The low-side driver drives an internal, ground-referenced low- $R_{DS(on)}$  N-Channel MOSFET. The voltage supply for the low-side driver is internally connected to the VCCD and PGND pins.

**High-Side Driver**

The high-side driver drives an internal, floating low- $R_{DS(on)}$  N-channel MOSFET. The gate voltage for the high side driver is developed by a bootstrap circuit referenced to Switch Node (VSW, PHASEF and PHASED) pins.

The bootstrap circuit is comprised of the integrated diode and an external bootstrap capacitor and resistor. When the NCP81382 is starting up, the VSW pin is at ground, allowing the bootstrap capacitor to charge up to VCCD through the bootstrap diode (See Figure 1). When the PWM input is driven high, the high-side driver will turn on the high-side MOSFET using the stored charge of the bootstrap capacitor. As the high-side MOSFET turns on, the voltage at the VSW, PHASEF and PHASED pins rise. When the high-side MOSFET is turned fully on, the switch node will settle to VIN and the BST pin will settle to VIN + VCCD (excluding parasitic ringing).

**Bootstrap Circuit**

The bootstrap circuit relies on an external charge storage capacitor ( $C_{BST}$ ) and an integrated diode to provide current to the HS Driver. A multi-layer ceramic capacitor (MLCC) with a value greater than 100 nF should be used as the bootstrap capacitor. An 4  $\Omega$  resistor in series with  $C_{BST}$  is recommended to decrease VSW overshoot.

**Power Supply Decoupling**

The NCP81382 will source relatively large currents into the MOSFET gates. In order to maintain a constant and stable supply voltage (VCCD) a low-ESR capacitor should be placed near the power and ground pins. A multi layer ceramic capacitor (MLCC) between 1  $\mu$ F and 4.7  $\mu$ F is typically used.

A separate supply pin (VCC) is used to power the analog and digital circuits within the driver. A 1  $\mu$ F ceramic capacitor should be placed on this pin in close proximity to the NCP81382. It is good practice to separate the VCC and VCCD decoupling capacitors with a resistor (10  $\Omega$  typical) to avoid coupling driver noise to the analog and digital circuits that control driver function (See Figure 1).

**Safety Timer and Overlap Protection Circuit**

It is important to avoid cross-conduction of the two MOSFETs which could result in a decrease in the power conversion efficiency or damage to the device.

The NCP81382 prevents cross conduction by monitoring the status of the MOSFET gates and applying the appropriate amount of non-overlap time (the time between the turn-off of one MOSFET and the turn-on of the other MOSFET). When the PWM input pin is driven high, the low-side MOSFET gate (GL) starts to go low after a propagation delay ( $tpdl_{GL}$ ). The time it takes for the low-side MOSFET to turn off is dependent on the low-side MOSFET gate charge. The high-side MOSFET gate begins to rise a fixed time ( $tpdh_{GH}$ ) after the GL voltage falls below the low-side MOSFET gate threshold.

When the PWM input pin is driven low, the high-side MOSFET gate (GH) starts to go low after a propagation delay ( $tpdl_{GH}$ ). The time it takes for the high-side MOSFET to turn off is dependent on the high-side MOSFET gate charge. The low-side MOSFET gate begins to rise a fixed time ( $tpdh_{GH}$ ) after the GH voltage falls below the high-side MOSFET gate threshold.

**Zero Current Detect Enable Input (ZCD\_EN)**

The ZCD\_EN pin is a logic input pin with an internal pull-up resistance to VCC.

When ZCD\_EN is set low, the NCP81382 will operate in synchronous rectifier (PWM) mode. This means that negative current can flow in the LS MOSFET if the load current is less than  $\frac{1}{2}$  delta current in the inductor. When ZCD\_EN is set high, Zero Current Detect PWM (ZCD\_PWM) mode will be enabled

With ZCD\_EN set high, when PWM rises above  $V_{PWM\_HI}$ , GL will go low and GH will go high after the non-overlap delay. Subsequently, if PWM falls to less than  $V_{PWM\_HI}$ , but stays above  $V_{PWM\_LO}$ , GL will go high after the non-overlap delay, and stay high for the duration of the ZCD Blanking + Debounce time ( $T_{BLNK}$ ). Once this timer has elapsed, VSW will be monitored for zero current, and GL will be pulled low when zero current is detected. The VSW zero current threshold undergoes an auto-calibration cycle every time DISB# is brought from low to high.

**PWM Input**

The PWM Input pin is a tri-state input used to control the HS MOSFET ON/OFF state. In conjunction with ZCD\_EN it also determines the state of the LS MOSFET. See Table 1 for logic operation. The PWM in some cases must operate with frequency programming resistances to ground. These resistances can range from 10 k $\Omega$  to 300 k $\Omega$  depending on the application. When SMOD# is set to > VSMOD#\_HI or to < VSMOD#\_LO, the input impedance to the PWM input is very high in order to avoid interferences with controllers that must use programming resistances on the PWM pin.



If  $V_{SMOD\#\_LO} < SMOD\# < V_{SMOD\#\_HI}$  (Mid-State), internal resistances will set undriven PWM pin voltage to Mid-State.

**Disable Input (DISB#)**

The DISB# pin is used to disable the GH to the High-Side FET to prevent power transfer. The pin has a pull-down resistance to force a disabled state when it is left unconnected. DISB# can be driven from the output of a logic device or set high with a pull-up resistance to VCC.

**VCC Undervoltage Lockout**

The VCC pin is monitored by an Undervoltage Lockout Circuit (UVLO). VCC voltage above the rising threshold enables the NCP81382.

**Table 2. UVLO/DISB# LOGIC TABLE**

UVLO	DISB#	Driver State
L	X	Disabled (GH = GL = 0)
H	L	Disabled (GH = GL = 0)
H	H	Enabled (See Table x)
H	Open	Disabled (GH = GL = 0)

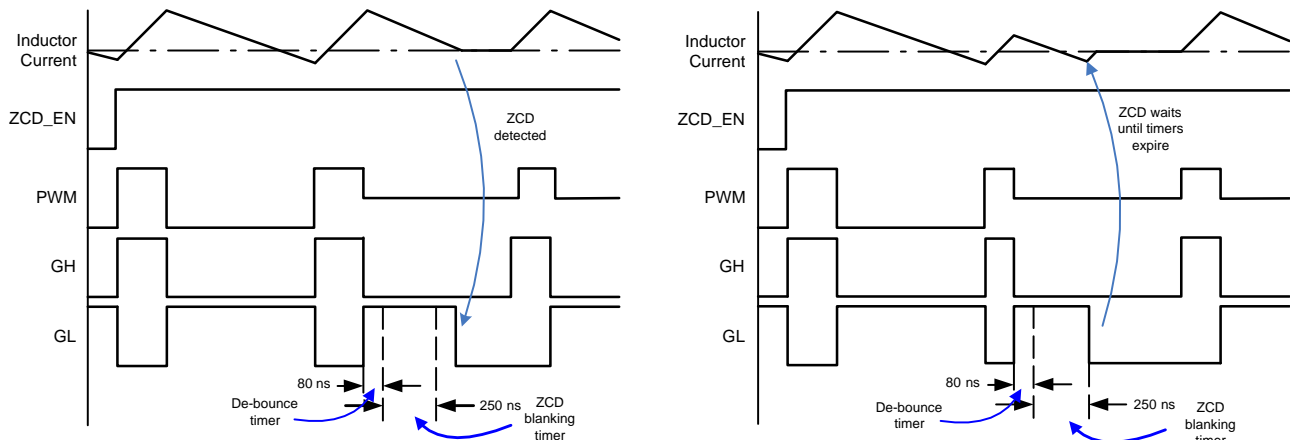
**Thermal Warning/Thermal Shutdown Output**

The THWN pin is an open drain output. When the temperature of the driver exceeds  $T_{THWN}$ , the THWN pin will be pulled low indicating a thermal warning. At this point, the part continues to function normally. When the temperature drops  $T_{THWN\_HYS}$  below  $T_{THWN}$ , the THWN pin will go high. If the driver temperature exceeds  $T_{THDN}$ , the part will enter thermal shutdown and turn off both MOSFETs. Once the temperature falls  $T_{THDN\_HYS}$  below  $T_{THDN}$ , the part will resume normal operation.

**Skip Mode Input (SMOD#)**

The SMOD# tri-state input pin has an internal pull-up resistance to VCC. When driven high, the SMOD# pin enables the low side synchronous MOSFET to operate independently of the internal ZCD function. When the SMOD# pin is set low during the PWM cycle it disables the low side MOSFET to allow discontinuous mode operation.

The NCP81382 has the capability of internally connecting a resistor divider to the PWM pin. To engage this mode, SMOD# needs to be placed into mid-state. While in SMOD# mid-state, the IC logic is equivalent to SMOD# being in the high state.

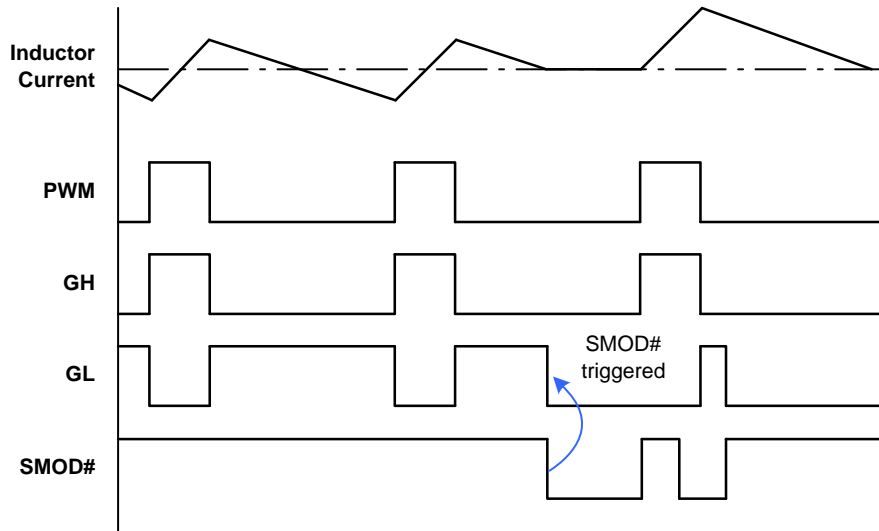


**Figure 6. PWM Timing Diagram**

NOTES: If the Zero Current Detect circuit detects zero current after the ZCD Wait timer period, the GL is driven low by the Zero Current Detect signal.

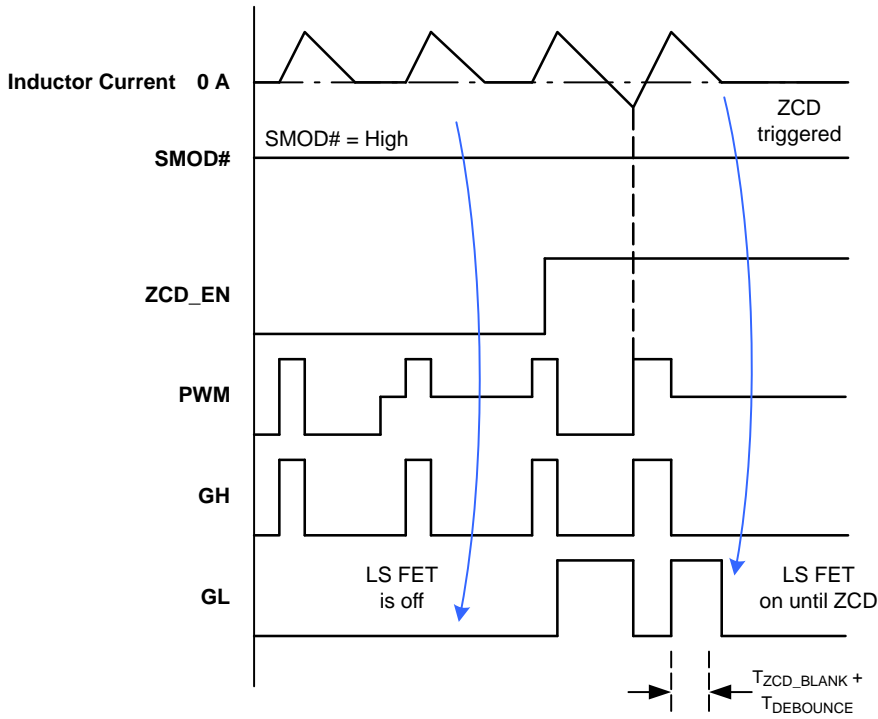
If the Zero Current Detect circuit detects zero current before the ZCD Wait timer period has expired, the Zero Current detect signal is ignored and the GL is driven low at the end of the ZCD Wait timer period.

# NCP81382



**Figure 7. SMOD# Timing Diagram**

NOTE: If the SMOD# input is driven low at any time after the GL has been driven high, the SMOD# Falling edge will trigger the GL to go low.  
 If the SMOD# input is driven low while the GH is high, the SMOD# input is ignored.



**Figure 8. ZCD\_EN Timing Diagram**

NOTE: When ZCD is enabled by pulling ZCD\_EN# high, the NCP81382 keeps the LS FET on until it detects zero current, reducing power loss.

# NCP81382

For Use with Controllers with 3-State PWM and No Zero Current Detection Capability:

**Table 3. LOGIC TABLE – 3-STATE PWM CONTROLLERS WITH NO ZCD**

PWM	SMOD#	ZCD_EN	GH	GL
H	H	H	ON	OFF
M	H	H	OFF	ZCD
L	H	H	OFF	ON

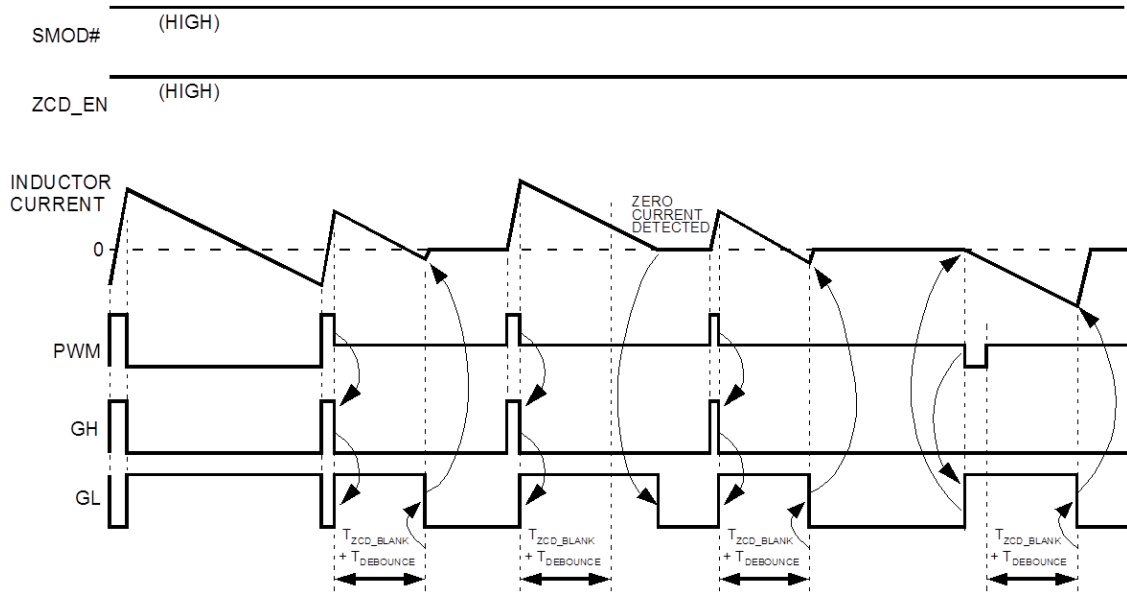
This section describes operation with controllers that are capable of 3 states in their PWM output and relies on the NCP81382 to conduct zero current detection during discontinuous conduction mode (DCM).

The SMOD# pin needs to either be set to 5 V or left disconnected. The NCP81382 has an internal pull-up resistor that connects to VCC that sets SMOD# to the logic high state if this pin is disconnected.

The ZCD\_EN pin needs to either be set to 5 V or left disconnected. The NCP81382 has an internal pull-up resistor connected to VCC that will set ZCD\_EN to the logic high state if this pin is left disconnected.

To operate the buck converter in continuous conduction mode (CCM), PWM needs to switch between the logic high and low states. To enter into DCM, PWM needs to be switched to the mid-state.

Whenever PWM transitions to mid-state, GH turns off and GL turns on. GL stays on for the duration of the de-bounce timer and ZCD blanking timers. Once these timers expire, the NCP81382 monitors the SW voltage and turns GL off when SW exceeds the ZCD threshold voltage. By turning off the LS FET, the body diode of the LS FET allows any positive current to go to zero but prevents negative current from conducting.



**Figure 9. Timing Diagram – 3-state PWM Controller, No ZCD**

# NCP81382

For Use with Controllers with 3-state PWM and Zero Current Detection Capability:

**Table 4. LOGIC TABLE – 3-STATE PWM CONTROLLERS WITH ZCD**

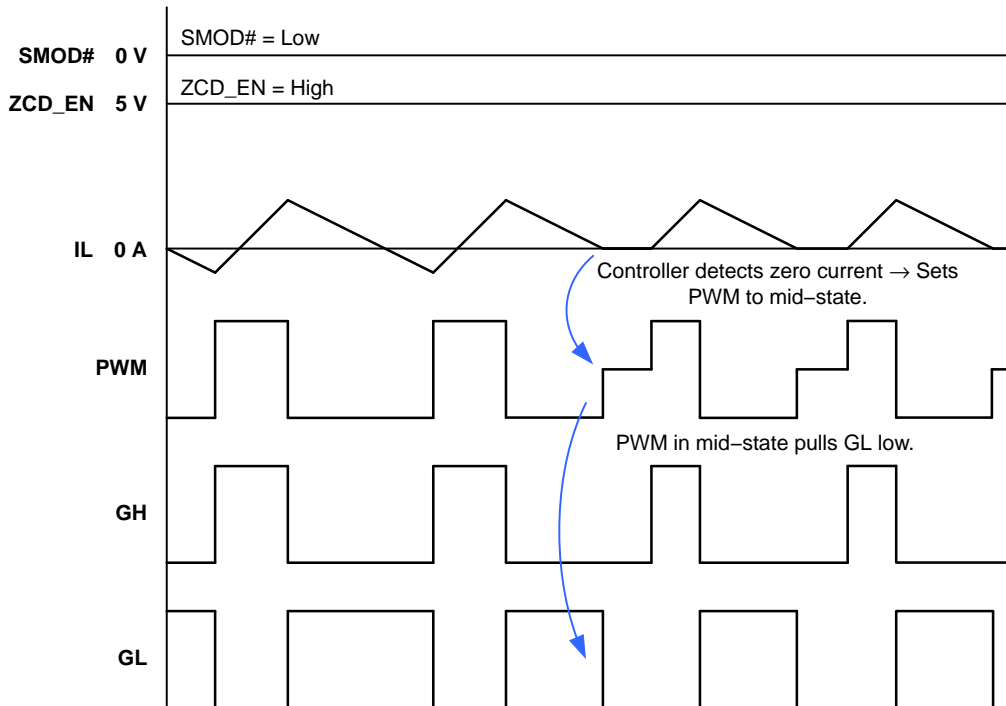
PWM	SMOD#	ZCD_EN	GH	GL
H	L	H	ON	OFF
M	L	H	OFF	OFF
L	L	H	OFF	ON

This section describes operation with controllers that are capable of 3 PWM output levels and have zero current detection during discontinuous conduction mode (DCM).

The SMOD# pin needs to be pulled low (below  $V_{SMOD\#\_LO}$ ).

The ZCD\_EN pin needs to either be set to 5 V or left disconnected. There is an internal pull-up resistor that connects to VCC and sets ZCD\_EN to the logic high state if this pin is left disconnected.

To operate the buck converter in continuous conduction mode (CCM), PWM needs to switch between the logic high and low states. During DCM, the controller is responsible for detecting when zero current has occurred, and then notifying the NCP81382 to turn off the LS FET. When the controller detects zero current, it needs to set PWM to mid-state, which causes the NCP81382 to pull both GH and GL to their off states without delay.



**Figure 10. Timing Diagram – 3-state PWM Controller, with ZCD**

# NCP81382

For Use with Controllers with 2-Level PWM and Zero Current Detection Capability:

Table 5. LOGIC TABLE – 2-STATE PWM CONTROLLERS WITH ZCD

PWM	SMOD#	ZCD_EN	GH	GL
H	L	X	ON	OFF
L	L	H	OFF	ON
L	L	L	OFF	OFF

This section describes operation with controllers that do not have 3-level PWM output capability but are capable of zero current detection during discontinuous conduction mode (DCM).

The SMOD# pin needs to be pulled low (below  $V_{SMOD\#\_LO}$ ).

When PWM is high, GH will always be in the high state and GL will always be in the low state, regardless of the state ZCD\_EN is in.

When PWM is in the low state, the state of ZCD\_EN determines whether the converter is placed into diode emulation mode. When the controller detects positive inductor current, ZCD\_EN should be in the high state, allowing the LS FET to be on and conducting. Once the controller detects zero or negative current, ZCD\_EN should be placed into the low state, turning off the LS FET. With the LS FET turned off, the body diode of the LS FET allows any positive current that may still be flowing to reach zero, but prevents the current from flowing in the negative direction.

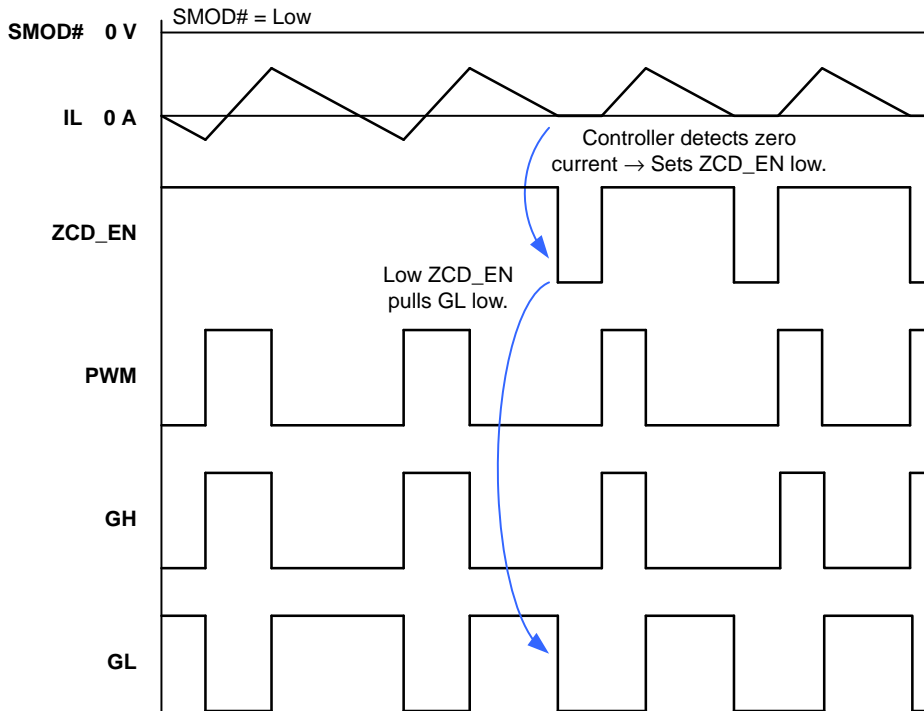


Figure 11. Timing Diagram – 2-state PWM Controller, with ZCD

# NCP81382

## Recommended PCB Layout (viewed from top)

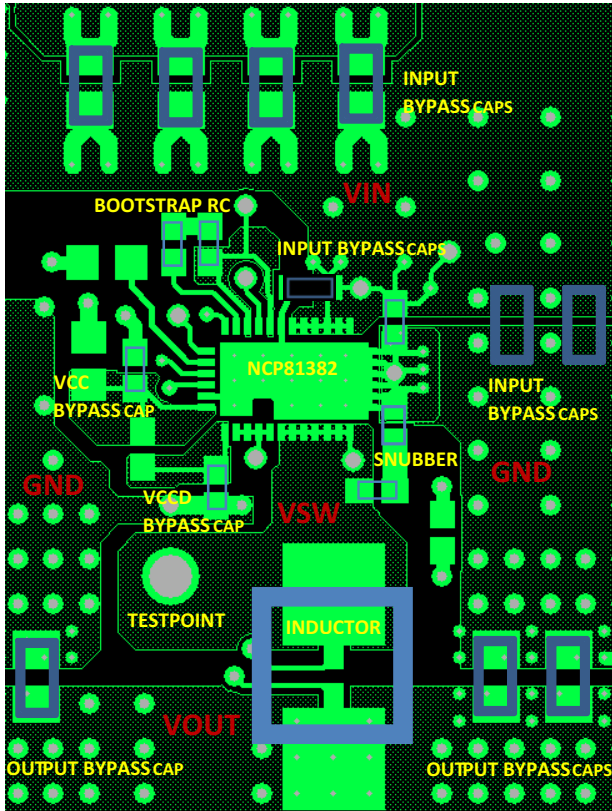


Figure 12. Top Copper Layer

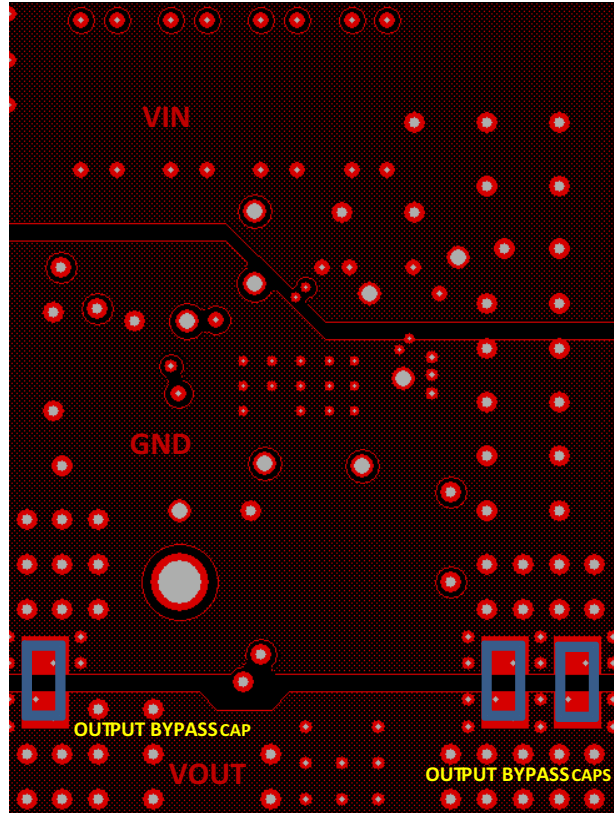


Figure 13. Bottom Copper Layer

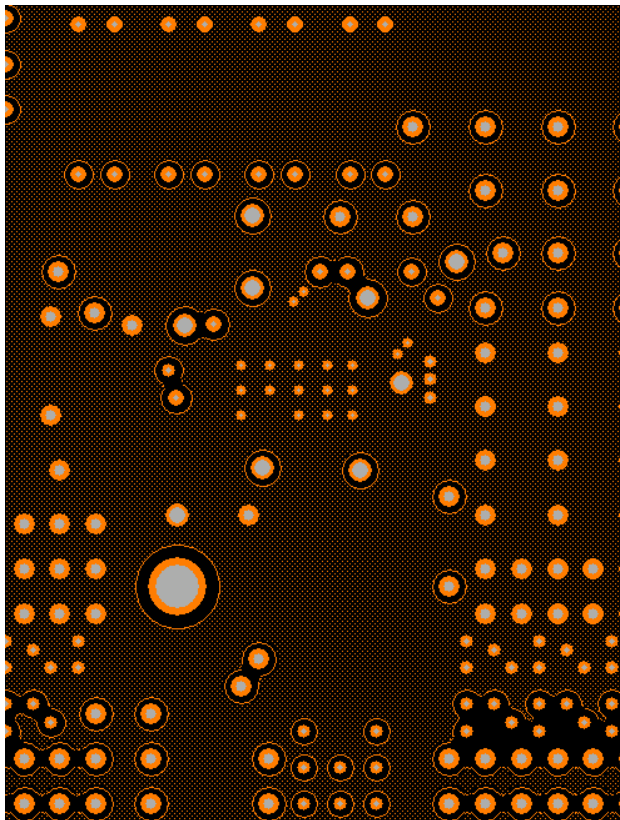


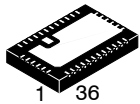
Figure 14. Layer 2 Copper Layer (Ground Plane)

Intel is a registered trademark of Intel Corporation in the U.S. and/or other countries.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

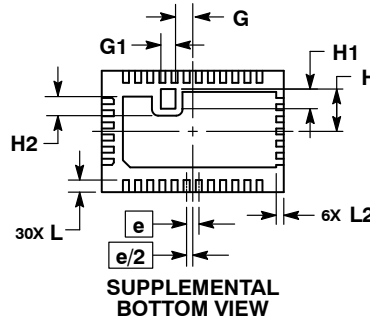
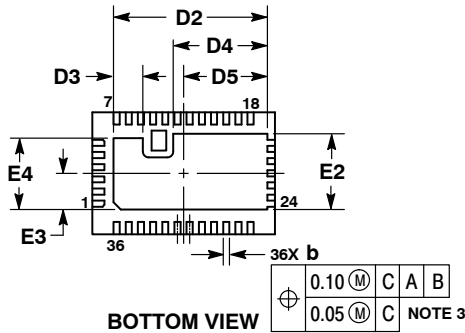
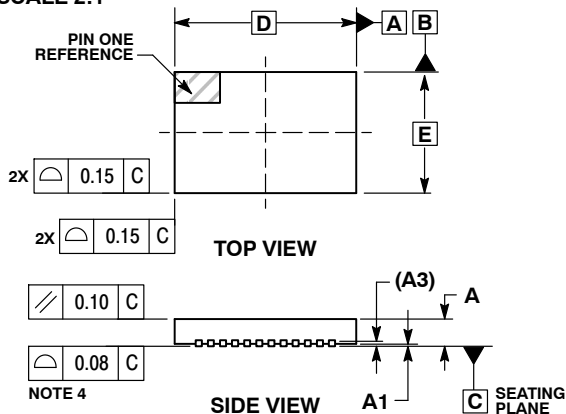
ON Semiconductor®



SCALE 2:1

**QFN36 6x4, 0.4P**  
CASE 485DZ  
ISSUE A

DATE 19 JUN 2015

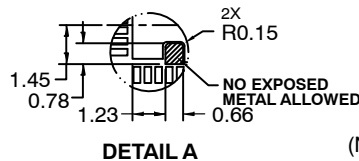
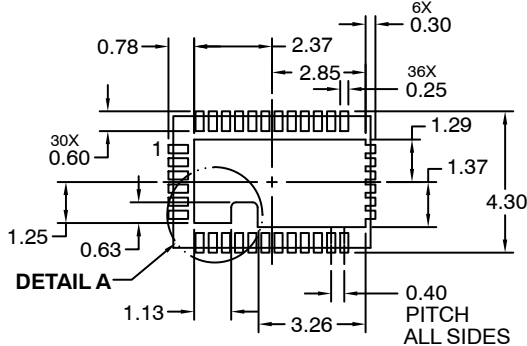


**NOTES:**

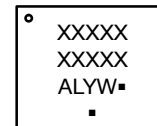
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.90	1.20
A1	0.00	0.05
A3	0.20	REF
b	0.15	0.25
D	6.00	BSC
D2	4.95	5.05
D3	0.91	1.01
D4	3.04	3.14
D5	2.70	2.80
E	4.00	BSC
E2	2.44	2.54
E3	1.14	1.24
E4	2.29	2.39
e	0.40	BSC
G	0.52	0.62
G1	0.43	0.53
H	1.35	1.45
H1	0.60	0.70
H2	0.57	0.68
L	0.30	0.50
L2	0.15	0.35

**RECOMMENDED SOLDERING FOOTPRINT\***



**GENERIC MARKING DIAGRAM\***



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

<b>DOCUMENT NUMBER:</b>	<b>98AON97081F</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>QFN36 6X4, 0.4P</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**onsemi Website:** [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

**North American Technical Support:**  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

**Europe, Middle East and Africa Technical Support:**

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative